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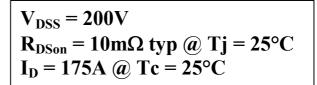


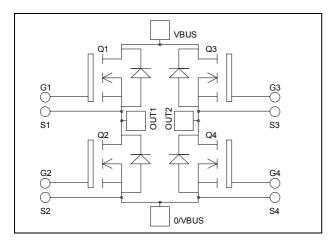






Full - Bridge MOSFET Power Module





0/VBU

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration



- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		200	V
Ţ	Continuous Drain Current	$T_c = 25$ °C	175	
I_D	Continuous Drain Current	$T_c = 80$ °C	131	Α
I_{DM}	Pulsed Drain current		700	
V_{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		12	mΩ
P_{D}	Maximum Power Dissipation $T_c = 25^{\circ}C$		694	W
I_{AR}	Avalanche current (repetitive and non repetitive)		89	A
E_{AR}	Repetitive Avalanche Energy		50	mJ
E_{AS}	Single Pulse Avalanche Energy		2500	IIIJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 200V$ $T_j = 25^{\circ}C$			200	μА
		$V_{GS} = 0V, V_{DS} = 160V$ $T_j = 125^{\circ}C$	C		1000	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 87.5A$		10	12	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5mA$			5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±150	nA

Dynamic Characteristics

•	Characteristic	Test Conditions	Min	Тур	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		13.7		
C_{oss}	Output Capacitance	$V_{DS} = 25V$		4.36		nF
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		0.19		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		224		
Q_{gs}	Gate – Source Charge	$V_{\text{Bus}} = 100V$		86		пC
Q_{gd}	Gate – Drain Charge	$I_{D} = 150A$		94		ļ
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		28		
T_{r}	Rise Time	$V_{GS} = 15V$ $V_{Bus} = 133V$ $I_D = 150A$		56		ns
$T_{d(off)}$	Turn-off Delay Time			81		
T_{f}	Fall Time	$R_G = 2.5\Omega$		99		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		926		т
E_{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 133V$ $I_D = 150A, R_G = 2.5\Omega$		910		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V$, $V_{Bus} = 133V$ $I_D = 150A$, $R_G = 2.5\Omega$		1216		т
E_{off}	Turn-off Switching Energy			1062		μJ

Source - Drain diode ratings and characteristics

Source - Drain Glode ratings and characteristics								
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit	
I_S	Continuous Source current		$Tc = 25^{\circ}C$			175	Α	
	(Body diode)		$Tc = 80^{\circ}C$			131	А	
$ m V_{SD}$	Diode Forward Voltage	$V_{GS} = 0V, I_S = -150A$				1.3	V	
dv/dt	Peak Diode Recovery •					8	V/ns	
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$			220	ns	
	Reverse Recovery Time	$I_S = -150A$ $V_R = 133V$	$T_j = 125$ °C			420	113	
Q _{rr}	Reverse Recovery Charge	$di_S/dt = 200A/\mu s$	$T_j = 25$ °C		2.14		μC	
		,	$T_j = 125$ °C		5.8		μС	

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \leq \text{-} \ 150 A \qquad \text{di/dt} \leq 700 A/\mu s \qquad V_R \leq V_{DSS} \qquad T_j \leq 150 ^{\circ} C$

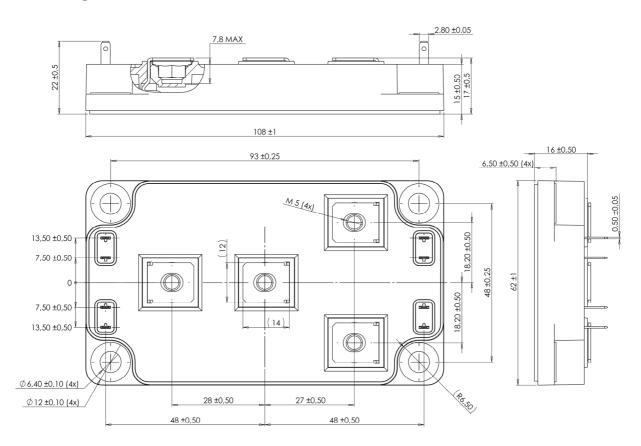
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Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance					0.18	°C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range		-40		150	°C	
T_{STG}	Storage Temperature Range			-40			125
$T_{\rm C}$	Operating Case Temperature			-40			100
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	11.111
Wt	Package Weight					300	g

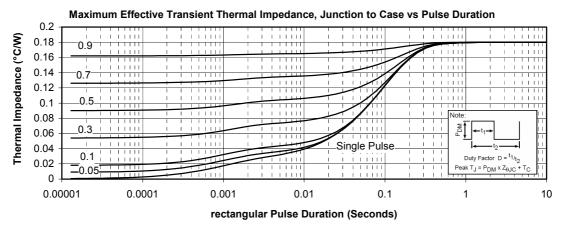
SP6 Package outline (dimensions in mm)

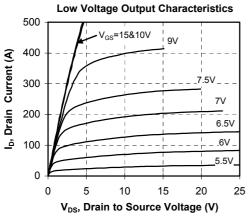


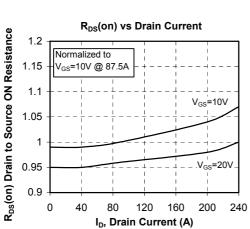
 $See \ application \ note \ APT0601 - Mounting \ Instructions \ for \ SP6 \ Power \ Modules \ on \ www.microsemi.com$

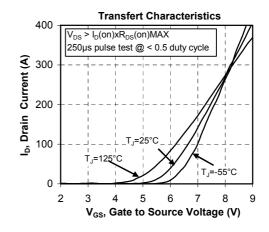


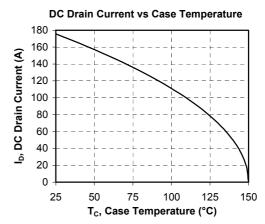
Typical Performance Curve





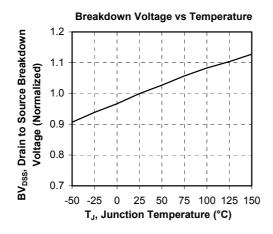


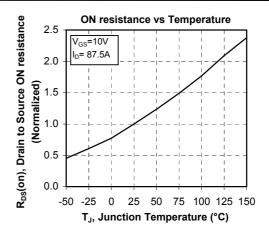


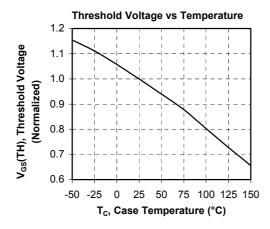


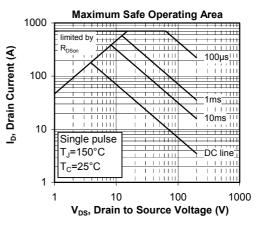
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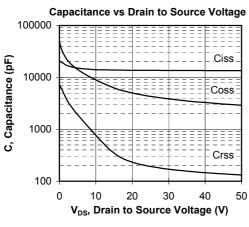


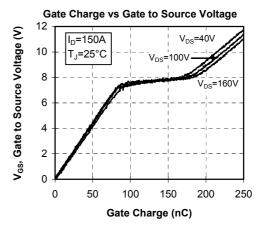






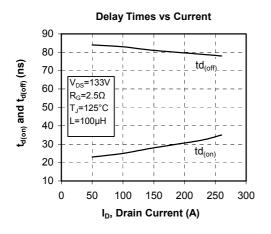


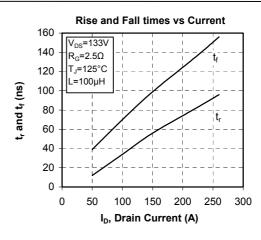


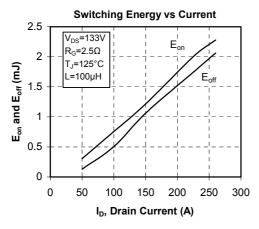


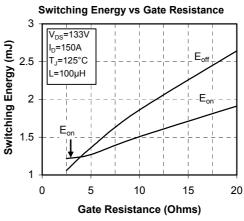
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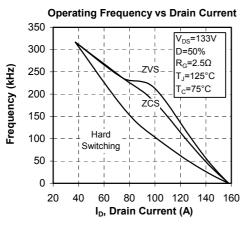


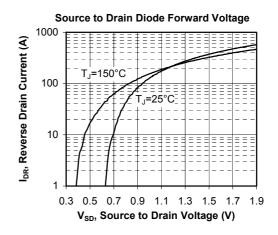














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